

Description

Features

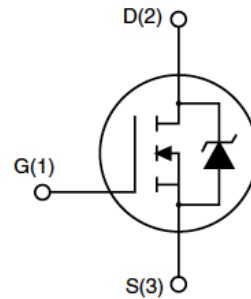
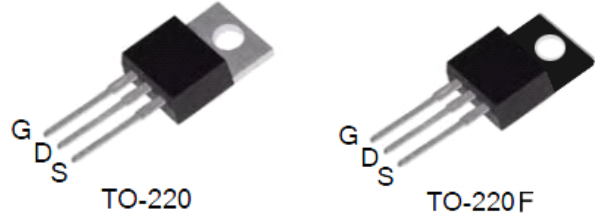
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V_{DSS}	$R_{DS(ON)}$ @ 10V (typ)	I_D
700V	1.2 Ω	6 A

- Fast switching
- 100% avalanche tested
- Improved dv/dt capability

Application

- High frequency switching mode power supply
- Uninterruptible Power Supply (UPS)
- Electronic ballast



Absolute Maximum Ratings $T_C=25^\circ\text{C}$ unless otherwise specified

Symbol	Parameter		TO-220	TO-220F	Units
V_{DSS}	Drain-Source Voltage		700		V
V_{GSS}	Gate-Source Voltage		± 30		V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	6	6*	A
		$T_C = 100^\circ\text{C}$	3.85	3.85*	A
I_{DM}	Pulsed Drain Current ^{note1}		24	24*	A
E_{AS}	Single Pulsed Avalanche Energy ^{note2}		180		mJ
dv/dt	Peak Diode Recovery Energy ^{note3}		4.5		V/ns
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	130	50	W
	Linear Derating Factor	$T_C > 25^\circ\text{C}$	1.04	0.4	W/ $^\circ\text{C}$
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.96	2.5	$^\circ\text{C}/\text{W}$
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150		$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Electrical Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise specified

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V,I _D = 250μA	700	-	-	V
ΔV _{(BR)DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	Reference to 25℃, I _D = 250μA	-	0.7	-	V/℃
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 700V, V _{GS} = 0V	-	-	1	μA
		V _{DS} = 560V, T _C = 125℃	-	-	10	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} = 0V, V _{GS} = ±30V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage ^{note4}	V _{DS} = V _{GS} , I _D = 250μA	2	-	4	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D = 3A	-	1.2	1.4	Ω
g _{FS}	Forward Transconductance	V _{DS} =30V, I _D = 3A	-	8	-	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	1230	-	pF
C _{oss}	Output Capacitance		-	98.2	-	pF
C _{rss}	Reverse Transfer Capacitance		-	5.29	-	pF
Q _g	Total Gate Charge	V _{DD} = 560V, I _D = 6A, V _{GS} = 10V	-	27.7	-	nC
Q _{gs}	Gate-Source Charge		-	4.75	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	9.81	-	nC
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 350V, I _D = 6A, RG = 10Ω, VGS = 10V	-	23	-	ns
t _r	Turn-On Rise Time		-	27.3	-	ns
t _{d(off)}	Turn-Off Delay Time		-	73.3	-	ns
t _f	Turn-Off Fall Time		-	28.5	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	6	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	24	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = 6A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _F = 6A,	-	459	-	ns
Q _{rr}	Reverse Recovery Charge	di/dt =100A/μs	-	3.5	-	uC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. $L = 10\text{mH}$, $I_{AS} = 6A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^{\circ}\text{C}$
3. $I_{SD} \leq 13A$, $di/dt \leq 200A/\mu s$, $V_{DD} \leq B_{VDSS}$, Starting $T_J = 25^{\circ}\text{C}$
4. Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

Typical Performance Characteristics

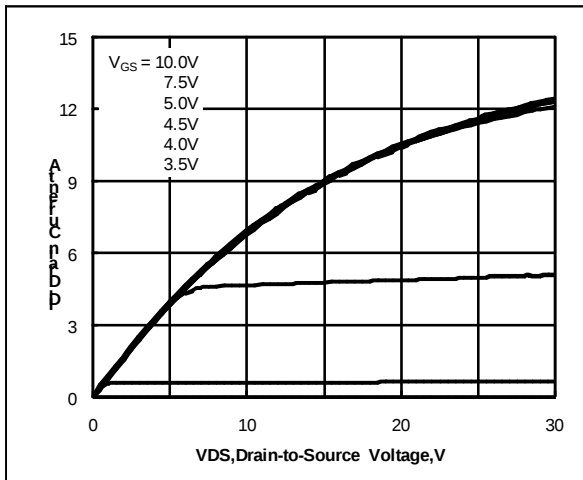


Figure 1. Output Characteristics

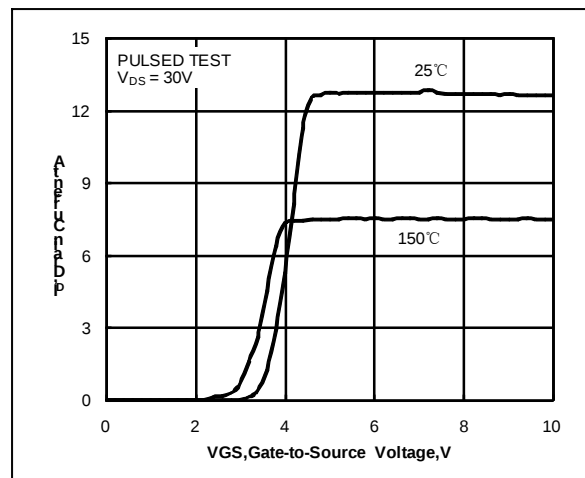


Figure 2. Transfer Characteristics

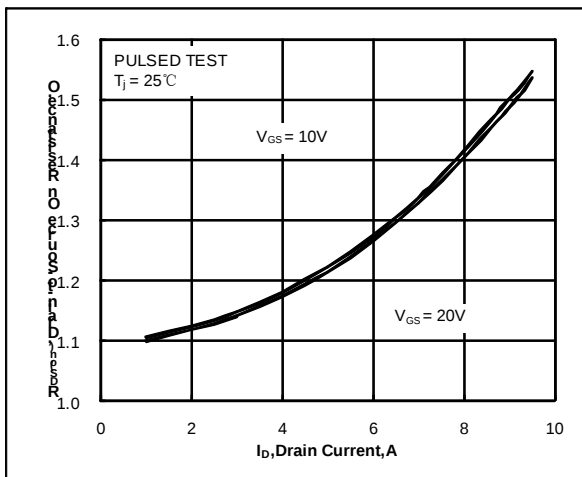


Figure 3. Drain-to-Source On Resistance vs. Drain Current and Gate Voltage

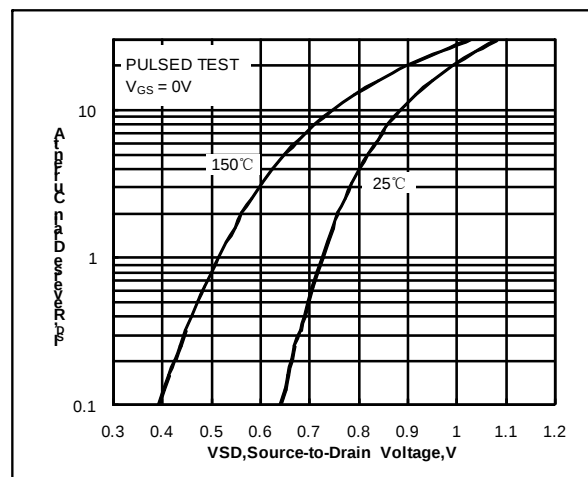


Figure 4. Body Diode Forward Voltage vs. Source Current and Temperature

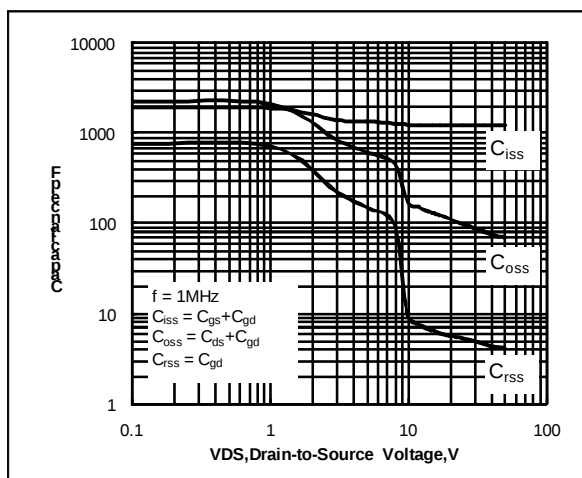


Figure 5. Capacitance Characteristics

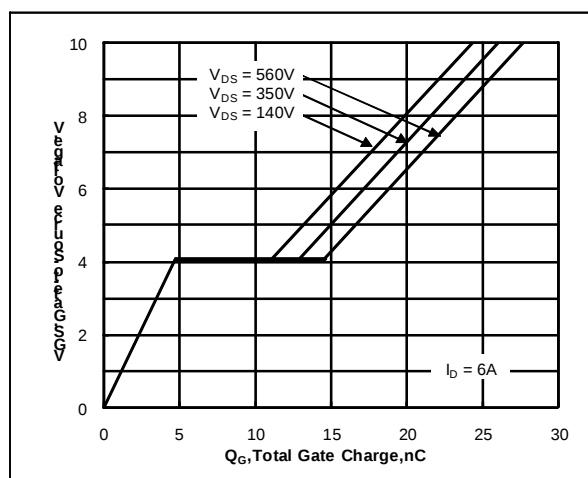


Figure 6. Gate Charge Characteristics

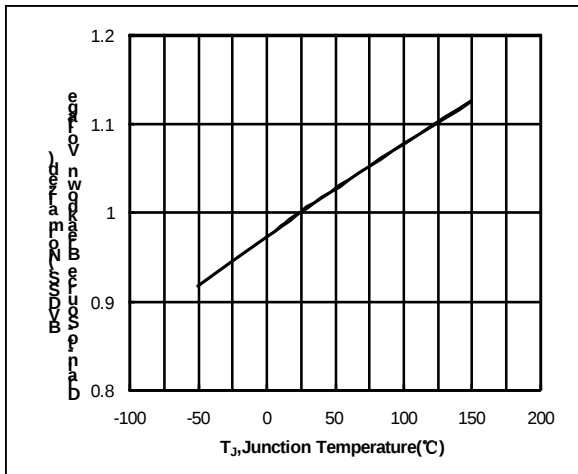


Figure 7. Normalized Breakdown Voltage vs. Junction Temperature

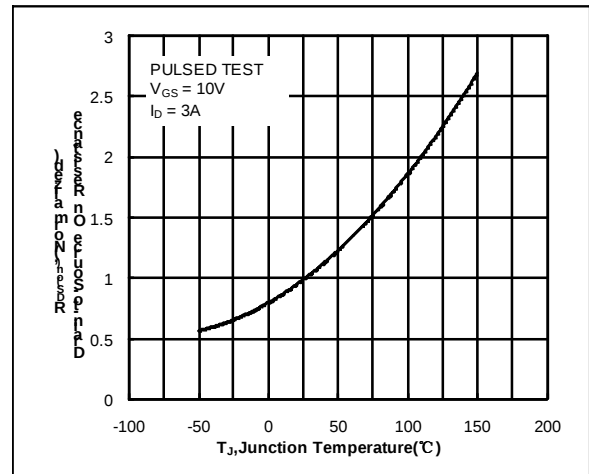


Figure 8. Normalized On Resistance vs. Junction Temperature

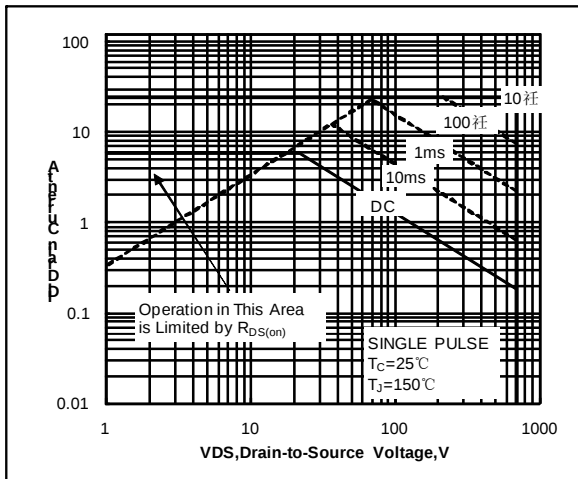


Figure 9. Maximum Safe Operating Area for RP6N70A

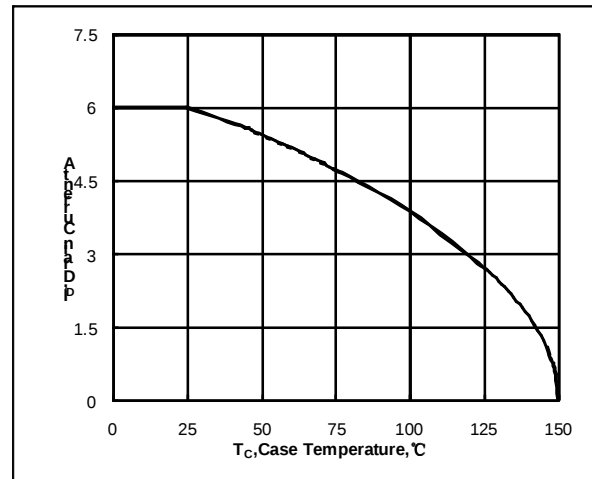


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

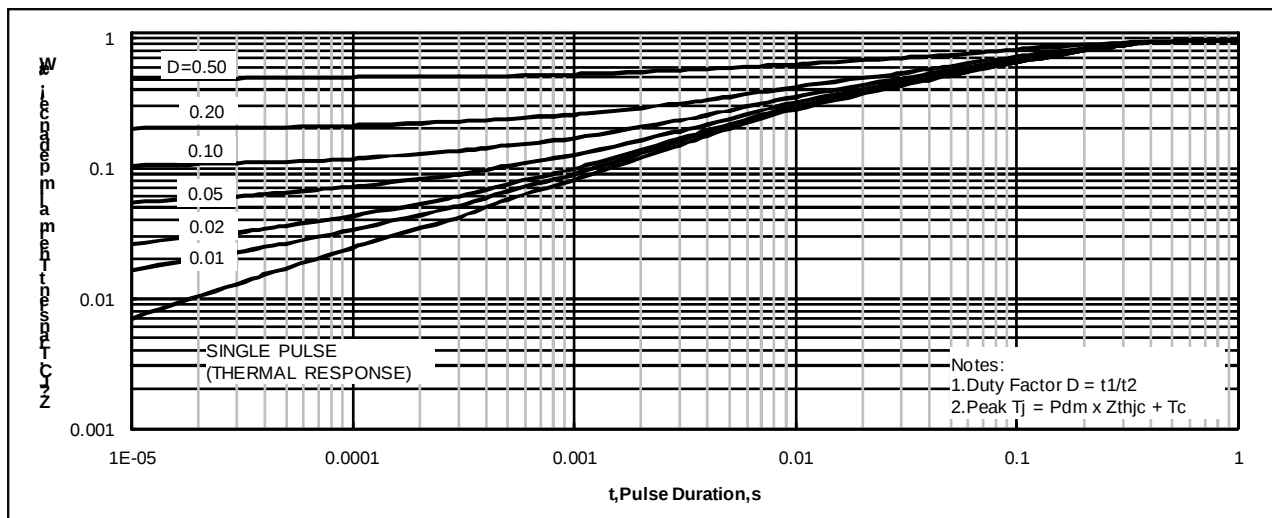


Figure 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case for RP6N70A

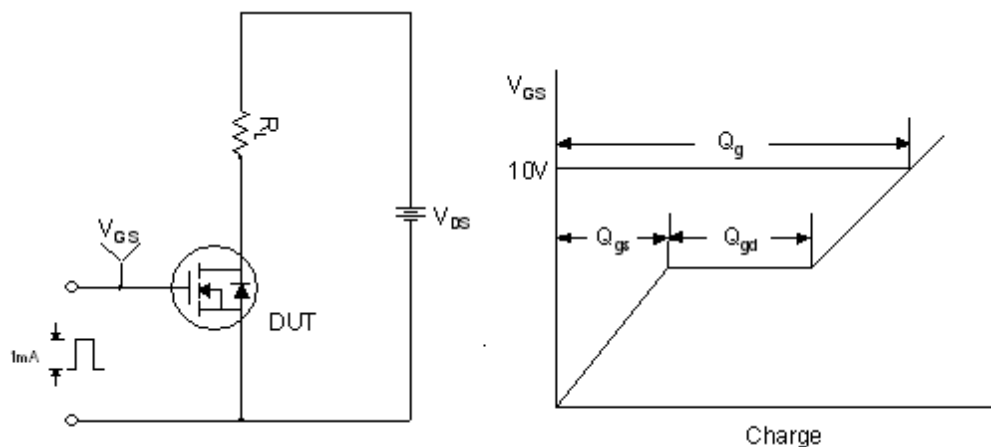


Figure 12. Gate Charge Test Circuit & Waveform

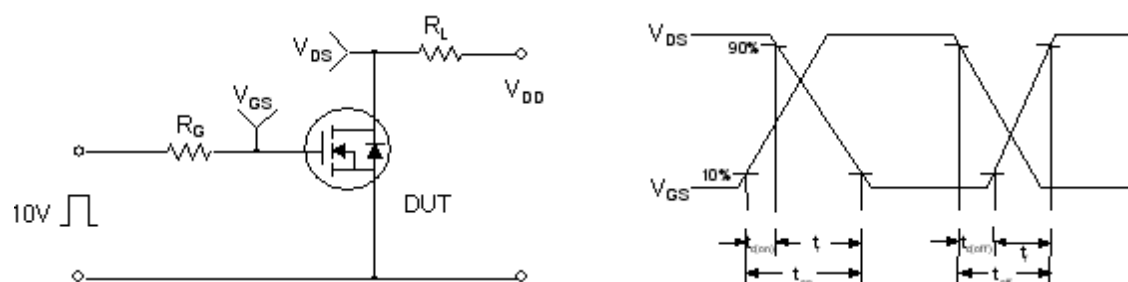


Figure 13. Resistive Switching Test Circuit & Waveforms

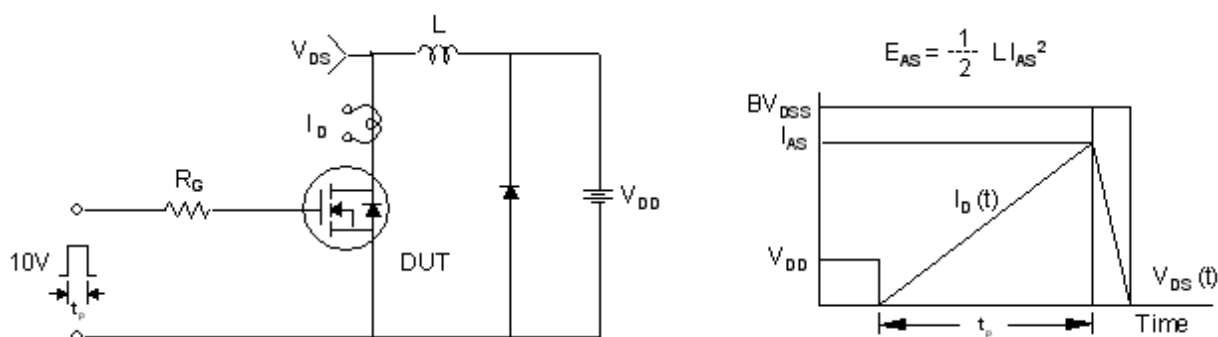


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

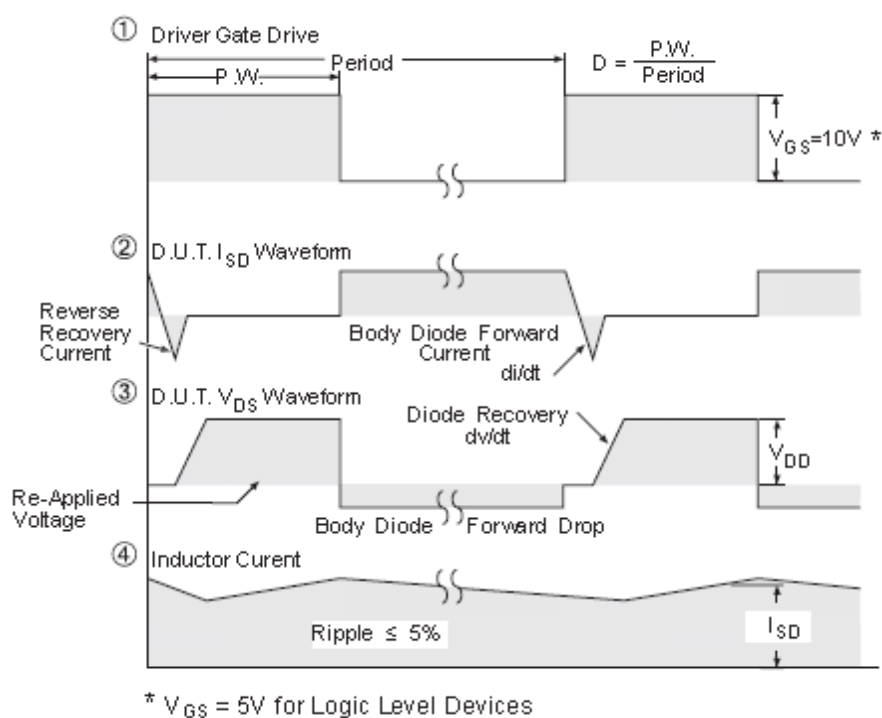
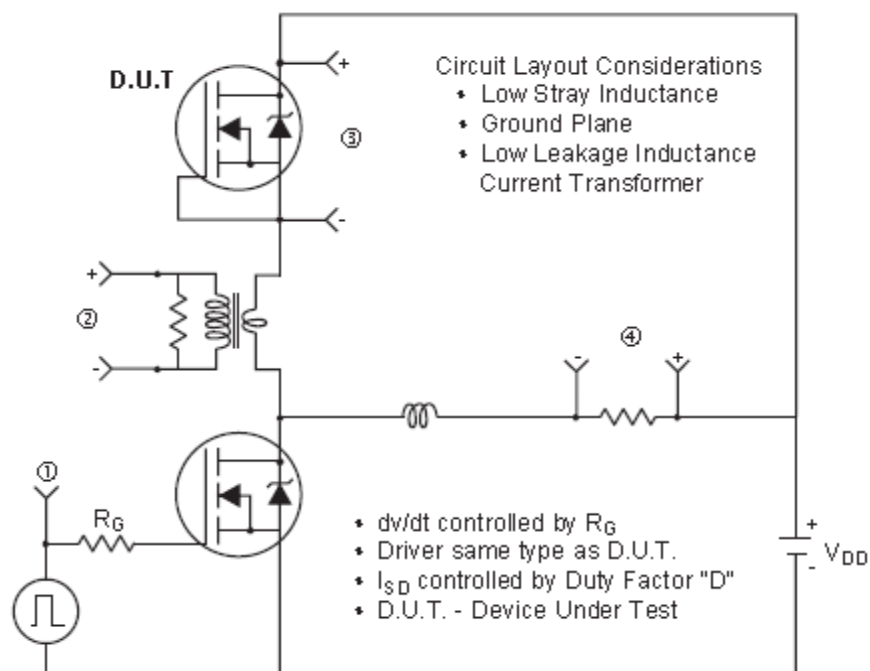


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms (For N-channel)